



#5/Amato  
PATENT  
Customer No. 22,852

Attorney Docket No. 04329/2222  
2/10/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
)  
Kouji MATSUO, et al. ) Group Art Unit: 2814  
)  
Serial No.: 09/492,780 ) Examiner: Rao, Shrinivas H.  
)  
Filed: January 28, 2000 )  
)  
For: SEMICONDUCTOR DEVICE AND )  
METHOD OF MANUFACTURING )  
THE SAME )

Assistant Commissioner for Patents  
Washington, DC 20231

Sir:

AMENDMENT

In reply to the Office Action dated November 4, 2002, with a period for response extending through February 4, 2003, Applicants amend the application as follows, and respectfully request the Examiner's reconsideration in view of the following remarks:

IN THE CLAIMS:

Please amend claim 12 as follows:

12. (Three Times Amended) A semiconductor device, comprising:
- a semiconductor substrate;
  - a metal-containing insulating film formed directly or indirectly on said semiconductor substrate, said metal-containing insulating film including a plurality of first insulating regions each of which is formed of a grain containing a metal oxide and a second insulating region

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